SGM7222

High Speed USB 2.0 (480Mbps) DPDT Analog Switch

GENERAL DESCRIPTION

The SGM7222 is a high-speed, low-power double-pole/double-throw (DPDT) analog switch that operates from a single +3.0V to +3.6V power supply.

SGM7222 is designed for the switching of high-speed USB 2.0 signals in handset and consumer applications, such as cell phones, digital cameras, and notebooks with hubs or controllers with limited USB I/Os.

The SGM7222 has low bit-to-bit skew and high channel-to-channel noise isolation, and is compatible with various standards, such as high-speed USB 2.0 (480 Mbps). Each switch is bidirectional and offers little or no attenuation of the high-speed signals at the outputs. Its bandwidth is wide enough to pass high-speed USB 2.0 differential signals (480 Mb/s) with good signal integrity.

The SGM7222 contains special circuitry on the D+/D-pins which allows the device to withstand a V_{BUS} short to D+ or D- when the USB devices is either powered off or powered on.

SGM7222 is available in Pb-free WQFN-10 and MSOP-10 packages. It operates over an ambient temperature range of -40 $\,$ to +85 $\,$.

APPLICATIONS

Route Signals for USB 2.0 MP3 and Other Personal Media Players Digital Cameras and Camcorders Portable Instrumentation Set-Top Box PDAs

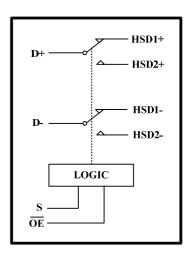
FEATURES

- Ron is Typically 4.5 Ω at +3.0V
- Low Bit-to-Bit Skew: 50ps (TYP)
- Voltage Operation: +3.0V to +3.6V
- Fast Switching Time:

ton 10ns toff 22ns

- Low Crosstalk: -41dB at 250MHz
- High Off-Isolation: -35dB at 250MHz
- Rail-to-Rail Input and Output Operation
- Break-Before-Make Switching
- Extended Industrial Temperature Range:
 -40 to +85
- Lead (Pb) Free WQFN-10 and MSOP-10 Packages

BLOCK DIAGRAM



ORDERING INFORMATION

MODEL	PIN- PACKAGE	SPECIFIED TEMPERATURE RANGE		ORDERING NUMBER	PACKAGE MARKING	PACKAGE OPTION		
CCM7000	MSOP-10	-40	to +85	SGM7222YMS10/TR	SGM7222YMS10	Tape and Reel, 3000		
SGM7222	WQFN-10	-40	to +85	SGM7222YWQ10/TR	7222	Tape and Reel, 3000		

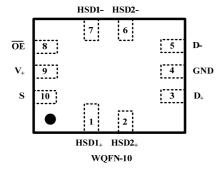
ABSOLUTE MAXIMUM RATINGS

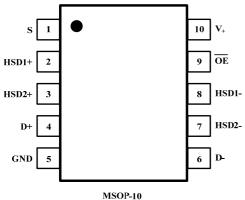
V+, IN to GND0	V to +4.6V
Analog, Digital voltage range0.3V to	o (V++0.3V)
Continuous Current NO, NC, or COM	±100mA
Peak Current NO, NC, or COM	±150mA
Operating Temperature Range40	to +85
Junction Temperature	+150

Storage Temperature65	to +150
Lead Temperature (soldering, 10s)	+260
ESD Susceptibility	
HBM	4000
MM	400

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

PIN CONFIGURATIONS (TOP VIEW)





PIN DESCRIPTION

PII	N	NAME	FUNCTION		
WQFN-10	MSOP-10	NAME			
9	10	V+	Power Supply		
4	5	GND	Ground		
10	1	S	Select Input		
8	9	ŌĒ	Output Enable		
1,2,	2,3,	HSD1+, HSD2+,			
7,6,	8,7,	HSD1-, HSD2-,	Data Ports		
3,5	4,6	D+, D-			

FUNCTION TABLE

ŌĒ	s	HSD1+ HSD1-	HSD2+ HSD2-		
0	0	ON	OFF		
0	1	OFF	ON		
1	×	OFF	OFF		

Switches Shown For Logic "0" Input

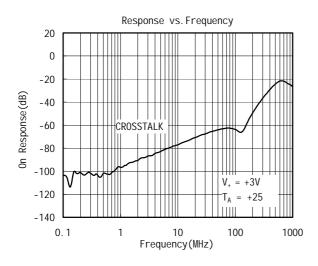
ELECTRICAL CHARACTERISTICS

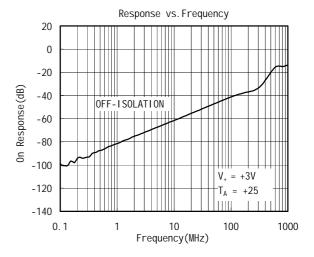
 $(V_{+}$ = +3.0V to +3.6V, GND = 0V, V_{IH} = +1.6V, V_{IL} = +0.5V, T_{A} = -40 to +85 . Typical values are at V_{+} = +3.3V, T_{A} = +25 , unless otherwise noted.)

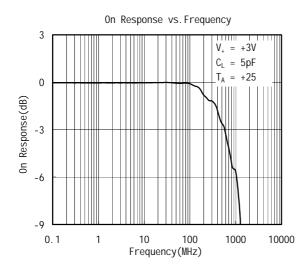
PARAMETER	SYMBOL	CONDITIONS	TEMP	MIN	TPY	MAX	UNITS
ANALOG SWITCH				•	•		
Analog I/O Voltage (HSD1+, HSD1-, HSD2+, HSD2-)	Vis		-40 to +85	0		V+	V
On-Resistance	Ron	V_{+} = 3.0V, V_{IS} = 0V to 0.4V, I_{D} = 8mA, Test Circuit 1	+25 -40 to +85		4.5		Ω
On-Resistance Match Between Channels	ΔR on	V ₊ = 3.0V, V _{IS} = 0V to 0.4V, I _D = 8mA, Test Circuit 1	+25 -40 to +85		0.15		Ω
On-Resistance Flatness	Rflat(on)	V+ = 3.0V, V _{IS} = 0V to 1.0V, I _D = 8mA, Test Circuit 1	+25		1.5		Ω
Power Off Leakage Current (D+, D-)	Ioff	V+= 0V, V_D = 0V to 3.6 V, Vs, $V_{\overline{OE}}$ = 0V or 3.6 V	-40 to +85			1	μΑ
Increase in I+ per Control Voltage	Ісст	$V_{+}=3.6V$, V_{S} or $V_{\overline{OE}}=2.6$ V	-40 to +85			5	μΑ
Source Off Leakage Current	IHSD2(OFF),IHSD1(OFF)	V+=3.6V, V _{IS} = 3.3V/ 0.3V, V _D = 0.3V/ 3.3V	-40 to +85			1	μΑ
Channel On Leakage Current	IHSD2(ON), IHSD1(ON)	$V_{+}=3.6V$, $V_{IS}=3.3V/0.3V$, $V_{D}=3.3V/0.3V$ or floating	-40 to +85			1	μΑ
DIGITAL INPUTS							
Input High Voltage	V _{IH}		-40 to +85	1.6			V
Input Low Voltage	VIL		-40 to +85			0.5	V
Input Leakage Current	IIN	$V_{+} = 3.0V$, V_{S} , $V_{\overline{OE}} = 0V$ or V_{+}	-40 to +85			1	μΑ
DYNAMIC CHARACTERISTI	CS						
Turn-On Time	ton	$V_{IS} = 0.8V$, $R_L = 50\Omega$, $C_L = 10pF$,	+25		10		ns
Turn-Off Time	toff	Test Circuit 2	+25		22		ns
Break-Before-Make Time Delay	to	$V_{IS} = 0.8V$, $R_L = 50\Omega$, $C_L = 10pF$, Test Circuit 3	+25		4		ns
Propagation Delay	t PD	$R_L = 50\Omega$, $C_L = 10pF$	+25		0.3		ns
Off Isolation	Oiso	Signal = 0dBm, R _L = 50Ω , f = 250MHz, Test Circuit 4	+25		-35		dB
Channel-to-Channel Crosstalk	Xtalk	Signal = 0dBm, R_L = 50 Ω , f = 250MHz, Test Circuit 5	+25		-41		dB
–3dB Bandwidth	BW	Signal = 0dBm, $R_L = 50\Omega$, $C_L = 5pF$ Test Circuit 6	+25		550		MHz
Channel-to-Channel Skew	tskew	$R_L = 50\Omega$, $C_L = 10pF$	+25		0.05		ns
Charge Injection Select Input to Common I/O	Q	$V_G = GND$, $C_L = 1.0$ nF, $R_G = 0\Omega$, $Q = C_L \times V_{OUT}$, Test Circuit 7	+25		11		рC
HSD+, HSD-, D+, D- ON Capacitance	Con		+25		6.5		pF
POWER REQUIREMENTS							
Power Supply Range	V+	-	-40 to +85	3.0		3.6	V
Power Supply Current	I+	$V_{+} = 3.0V$, V_{S} , $V_{\overline{OE}} = 0V$ or V_{+}	-40 to +85			1	μΑ

Specifications subject to changes without notice.

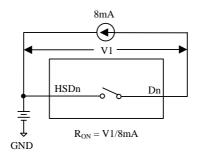
TYPICAL PERFORMANCE CHARACTERISTICS



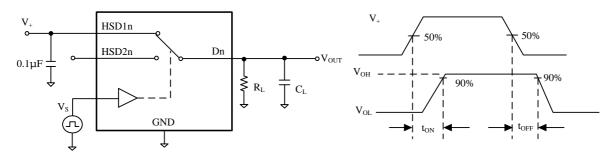




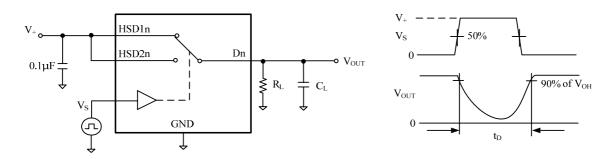
TEST CIRCUITS



Test Circuit 1. On Resistance

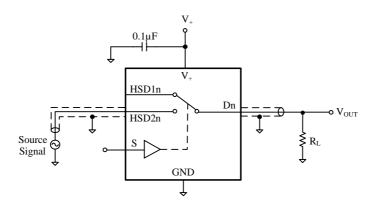


Test Circuit 2. Switching Times (ton, toff)

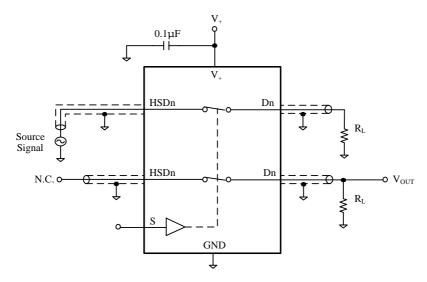


Test Circuit 3. Break-Before-Make Time (tD)

TEST CIRCUITS (Cont.)



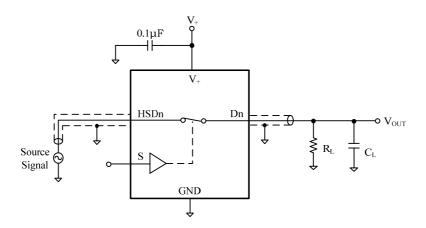
Test Circuit 4. Off Isolation



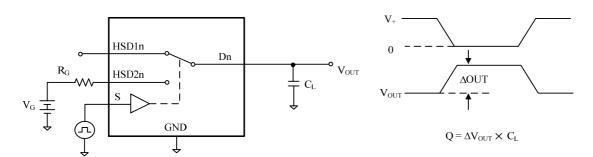
Channel To Channel Crosstalk = -20 $\times \log \frac{V_{HSDn}}{V_{OUT}}$

Test Circuit 5. Channel-to-Channel Crosstalk

TEST CIRCUITS (Cont.)



Test Circuit 6. -3dB Bandwidth



Test Circuit 7. Charge Injection (Q)

APPLICATION NOTES

Power-Off Protection

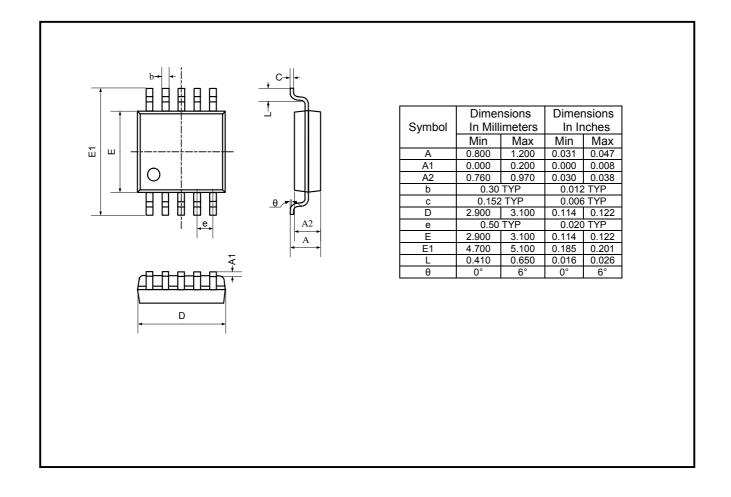
For a V_{BUS} short circuit, the switch is expected to withstand such a condition for at least 24 hours. The SGM7222 has specially designed circuitry which prevents unintended signal bleed through as well as guaranteed system reliability during a power-down, over-voltage condition. The protection has been added to the common pins (D+, D-).

Power-On Protection

The USB 2.0 specification also notes that the USB device should be capable of withstanding a V_{BUS} short during transmission of data. This modification works by limiting current flow back into the V+ rail during the over-voltage event so current remains within the safe operating range. In this application, the switch passes the full 5.25V input signal through to the selected output, while maintaining specified off isolation on the un-selected pins.

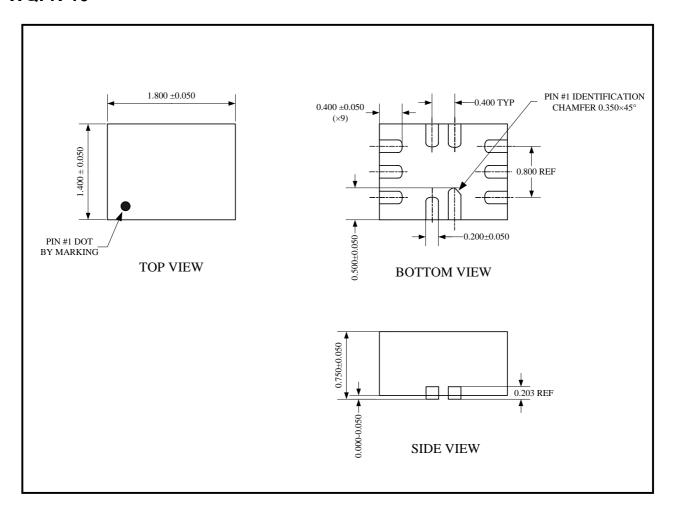
PACKAGE OUTLINE DIMENSIONS

MSOP-10



PACKAGE OUTLINE DIMENSIONS

WQFN-10



Note: All linear dimensions are in millimeters.

REVISION HISTORY

Location Page

03/2008—Preliminary Datasheet

SG Micro Ltd.

A2608, NO.72 North Road Xisanhuan, Haidian District, Beijing, China 100037 Tel: 86-10-51798160/80

Fax: 86-10-51798180-803 www.sg-micro.com